

Abstract of the Disclosure

A method for fabricating a capacitor of a semiconductor device which includes the steps of: forming an inter-layer insulating layer on a substrate; forming a contact hole exposing a partial portion of the substrate by etching the inter-layer insulating layer; a storage node contact buried into the contact hole such that the surface of the storage node contact is at the same plane level as the surface of the inter-layer insulating layer; forming a storage node oxide layer on the inter-layer insulating layer; forming a storage node hole exposing the storage node contact by etching the storage node oxide layer; forming a supporting hole hollowed in downward direction by recessing or removing partially an upper portion of the exposed storage node contact; and forming a storage node having a cylinder structure and being electrically connected to the storage node contact.